

**Learning Objective: Electric Field and Potential Due to Point Charges**

**Problem 1.** Two point charges with  $q_1 = 20 \mu\text{C}$  and  $q_2 = -40 \mu\text{C}$  are located in a free space at points with Cartesian coordinates  $(1, 3, -1)$  m and  $(-3, 1, -2)$  m, respectively.

- (a) Determine the force  $\mathbf{F}_1$  acting on charge  $q_1$ .
- (b) Find the electric field  $\mathbf{E}$  at  $(3, 1, -2)$  m.
- (c) Suppose a new point charge  $q_3 = 80 \mu\text{C}$  is placed at  $(3, 1, -2)$  m, determine the force  $\mathbf{F}_3$  acting on charge  $q_3$ .

**Learning Objective: Electric Field and Potential Due to Charge Distribution**

**Problem 2.** A charge  $+Q$  is evenly spread along the  $x$ -axis from  $x = -L/2$  to  $x = L/2$ .

- (a) Determine the line charge density  $\rho_L$ .
- (b) Derive an expression of the electric field  $\mathbf{E}$  along the  $x$ -axis where  $a > L/2$ .
- (c) Derive an expression of the electric potential  $V$  along the  $x$ -axis where  $a > L/2$ .
- (d) Derive an expression of the electric field  $\mathbf{E}$  at  $y = a$  where  $a > 0$ .

**Problem 3.** Consider a ring of radius  $r = a$  in the  $z = 0$  plane, centered at the origin, has a uniform line charge density  $\rho_L$ . Another circular disk of radius  $r = a$  in the  $z = d$  plane ( $d > 0$ ), centered at the origin, has a uniform surface charge density  $\rho_s$ .

- (a) Derive an expression of the electric field  $\mathbf{E}$  along the  $z$ -axis where  $0 < z < d$ .
- (b) Derive an expression of the electric field  $\mathbf{E}$  along the  $z$ -axis where  $z > d$ .

**Learning Objective: Gauss's Law**

**Problem 4.** Consider a sphere of radius  $r = a$  centered at the origin has a uniform volume charge density  $\rho_v$  in a spherical coordinate.

- (a) Determine the electric field  $\mathbf{E}$  for  $r > a$ .
- (b) Determine the electric field  $\mathbf{E}$  for  $0 < r < a$ .

**Learning Objective: Capacitance**

**Problem 5.** Consider an n-channel MOSFET with a gate oxide thickness of 10 nm, gate width of 25  $\mu\text{m}$  and gate length of 1  $\mu\text{m}$ . A non-zero gate-to-source voltage  $V_{\text{GS}}$  is applied. Use  $\epsilon_{ox} = 3.9\epsilon_0$ ,  $n_i = 1.5 \times 10^{10} \text{ cm}^{-3}$  if needed.

- (a) Determine the gate capacitance of the MOSFET.
- (b) Determine the total charge at the gate.
- (c) Determine the electric field inside the oxide.